

REVISIONS

DCP #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRD	DATE
1262	A	RELEASED	HO	8/27/02	JWM	8/27/02	DJC	8/27/02

Dimensions	A	B	C	D	E	F	G	H	I	J	K
Min.	8.50	7.74	6.09	0.40	-	2.41	4.82	0.71	0.73	12.70	42°
Max.	9.39	8.50	6.60	0.53	0.88	2.66	5.33	0.86	1.02	-	48°

This is a silicon PNP transistor in a TO-39 type case designed primarily for amplifier and switching applications. This device features high breakdown voltage, low leakage current, low capacity, and beta useful over an extremely wide current range.

Electrical Characteristics: (T_A = +25°C Unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 100mA, I _B = 0	40	-	-	V
Collector Cut-Off Current	I _{CBO}	V _{CE} = 40V, I _E = 0	-	-	100	µA
Emitter Cut-Off Current	I _{EBO}	V _{BE} = 7V, I _C = 0	-	-	500	µA

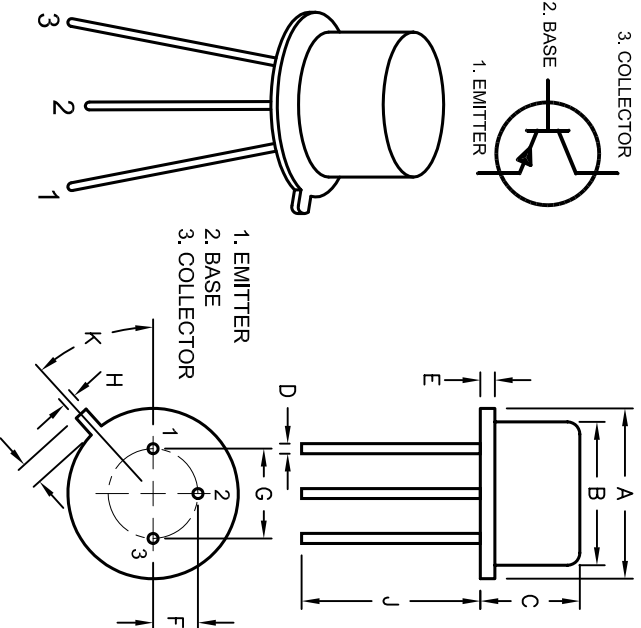
ON Characteristics, Note 1

DC Current Gain	h _{FE}	V _{CE} = 1V, I _C = 100mA				
		V _{CE} = 1V, I _C = 250mA	V _{CE} = 1V, I _C = 500mA	V _{CE} = 1V, I _C = 1A		
		30	20	10		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 1A, I _B = 125mA	-	-	0.6	V
Base-Emitter On Voltage	V _{BE(sat)}	I _C = 1A, I _B = 100mA	-	-	1.5	V

Small-Signal Characteristics

Small-Signal Current Gain	h _{ie}	V _{CE} = 10V, I _C = 50mA, f = 1KHz	25	-	-
Output Capacitance	C _{obo}	V _{GB} = 10V, f = 0.1MHz	-	-	100
Input Capacitance	C _{ibo}	V _{BE} = 500mV, f = 1MHz	-	-	110

Note 1. Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤ 1%.



Absolute Maximum Ratings:

- Collector-Base Voltage, V_{CB0} = 40V
- Collector-Emitter Voltage, V_{CE0} = 40V
- Emitter-Base Voltage, V_{EB0} = 7V
- Continuous Collector Current, I_C = 1A
- Total Device Dissipation (T_A = +25°C), P_D = 1W
Derate above 25°C = 5.7mW/°C
- Total Device Dissipation (T_C = +25°C), P_D = 6W
Derate above 25°C = 34mW/°C
- Operating Junction Temperature Range, T_J = -65° to +200°C
- Storage Temperature Range, T_{stg} = -65° to +200°C
- Thermal Resistance, Junction-to-Case, R_{th(jc)}: 29°C/W
- Lead temperature (During Soldering, 1/16" from case, 60sec max), T_L: 300°C

DISCLAIMER:
ALL STATEMENTS AND TECHNICAL INFORMATION CONTAINED HEREIN ARE BASED UPON INFORMATION AND/OR TESTS WE BELIEVE TO BE ACCURATE AND RELIABLE. SINCE CONDITIONS OF USE ARE BEYOND OUR CONTROL, THE USER SHALL DETERMINE THE SUITABILITY OF THE PRODUCT FOR THE INTENDED USE AND ASSUME ALL RISK AND LIABILITY WHATSOEVER IN CONNECTION THEREWITH.

TOLERANCES:

UNLESS OTHERWISE SPECIFIED, DIMENSIONS ARE FOR REFERENCE PURPOSES ONLY.

DRAWN BY:	DATE:	DRAWING TITLE:	SCALE:	U.O.M.:	SHEET:	OF
HISHAM ODISH	8/27/02	Transistor, Amplifier, Switching, Bipolar, TO-39, PNP	NTS	Millimeters	1	1
CHECKED BY:	DATE:					
JEFF MCWICKER	8/27/02	SIZE	DWG. NO.	ELECTRONIC FILE	REV	
APPROVED BY:	DATE:	A	2N4234	35C0713.DWG	A	
DANIEL CAREY	8/27/02					